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Docket: AM-5825

3600.5825
August 21, 2002 (12:28PM)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Diana Xiaobing MA **Attorneys Docket:** AM-5825

Serial No.: 09/922,980 **Art Unit No.:** 2825

Filed: August 6, 2001 **Examiner:** R. Rocchegiani

For: "INTEGRATED SYSTEM FOR OXIDE ETCHING AND METAL LINER DEPOSITION"

Commissioner of Patents
Washington, DC 20231

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RESPONSE TO RESTRICTION REQUIREMENT AND AMENDMENT UNDER 37 CFR §1.115

Sir:

In a Preliminary Amendment for consideration before initial examination, please amend the above application as follows:

In the specification:

Two Paragraphs at page 2, line 14 to page 3, line 15:

A1

Conventionally, the inter-level dielectric layers have been oxide layers formed of silica of the approximate composition SiO_2 or related silicate glasses such as borophosphosilicate glass (BPSG). However, these materials have a relatively high dielectric constant k of about 3.9 but even with process variations the value is limited to $k<4.0$. In view of the increased operating frequencies of advanced integrated circuits and the reduced spacing between conductive features, such as buses, there has been much recent development in low-k inter-level dielectric materials having reduced dielectric constants of less than 3.9. Doped silica such as fluorosilicate glass (FSG) has a dielectric constant of somewhat over 3. Other low-k dielectrics are being developed